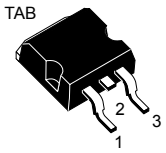
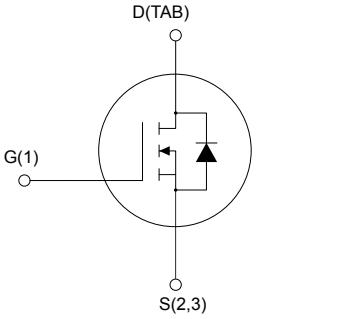
SCT10N120H

Datasheet

Silicon carbide Power MOSFET 1200 V, 13 A, 500 mΩ (typ., T_J=25 °C), in an H²PAK-2 package



H²PAK-2



NCHG1DTABS23

Features

- Very tight variation of on-resistance vs temperature
- Very high operating temperature capability (T_J = 175 °C)
- Very fast and robust intrinsic body diode
- Low capacitance

Application

- High voltage DC-DC converters
- Switch mode power supplies

Description

This silicon carbide Power MOSFET is produced exploiting the advanced, innovative properties of wide bandgap materials. This results in unsurpassed on-resistance per unit area and very good switching performance almost independent of temperature. The outstanding thermal properties of the SiC material allow designers to use an industry-standard outline with significantly improved thermal capability. These features render the device perfectly suitable for high-efficiency and high power density applications.

Product status link
SCT10N120H

Product summary	
Order code	SCT10N120H
Marking	SCT10N120
Package	H²PAK-2
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	1200	V
V_{GS}	Gate-source voltage	-10 to 25	V
I_D	Drain current (continuous) at T_C = 25 °C	13	A
I_D	Drain current (continuous) at T_C = 100 °C	10	A
I_{DM} (1)	Drain current (pulsed)	30	A
P_{TOT}	Total power dissipation at T_C = 25 °C	130	W
T_{stg}	Storage temperature range	-55 to 175	°C
T_j	Operating junction temperature range		°C

1. *Pulse width limited by safe operating area.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.17	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	40	°C/W

1. *When mounted on 1 inch² FR-4 board, 2 oz Cu.*

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified).

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	1200			V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 1200 V, V_{GS} = 0 V			10	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = -10 to 22 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	1.8	3.5		V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 20 V, I_D = 6 A		500	690	mΩ
		V_{GS} = 20 V, I_D = 6 A, T_J = 150 °C		520		mΩ
		V_{GS} = 20 V, I_D = 6 A, T_J = 175 °C		540		mΩ

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 400 V, f = 1 MHz, V_{GS} = 0 V	-	290	-	pF
C_{oss}	Output capacitance		-	30	-	pF
C_{rss}	Reverse transfer capacitance		-	9	-	pF
Q_g	Total gate charge	V_{DD} = 800 V, I_D = 6 A, V_{GS} = 0 to 20 V	-	22	-	nC
Q_{gs}	Gate-source charge		-	3	-	nC
Q_{gd}	Gate-drain charge		-	10	-	nC
R_g	Gate input resistance	f = 1 MHz, I_D = 0 A	-	8	-	Ω

Table 5. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	V_{DD} = 800 V, I_D = 6 A, R_G = 10 Ω, V_{GS} = -5 to 20 V	-	90	-	µJ
E_{off}	Turn-off switching energy		-	30	-	µJ
E_{on}	Turn-on switching energy	V_{DD} = 800 V, I_D = 6 A, R_G = 10 Ω, V_{GS} = -5 to 20 V, T_J = 150 °C	-	104	-	µJ
E_{off}	Turn-off switching energy		-	33	-	µJ

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 800 V, I_D = 6 A, R_G = 10 Ω, V_{GS} = -5 to 20 V	-	7	-	ns
t_f	Fall time		-	17	-	ns
$t_{d(off)}$	Turn-off delay time		-	14	-	ns
t_r	Rise time		-	12	-	ns

Table 7. Reverse SiC diode characteristics

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
V_{SD}	Diode forward voltage	I_F = 6 A, V_{GS} = 0 V	-	2.5	-	V
t_{rr}	Reverse recovery time	I_{SD} = 6 A, di/dt = 2000 A/µs V_{DD} = 800 V, T_J= 150 °C	-	16	-	ns
Q_{rr}	Reverse recovery charge		-	107	-	nC
I_{RRM}	Reverse recovery current		-	12	-	A

2.1 Electrical characteristics curves

Figure 1. Normalized thermal impedance

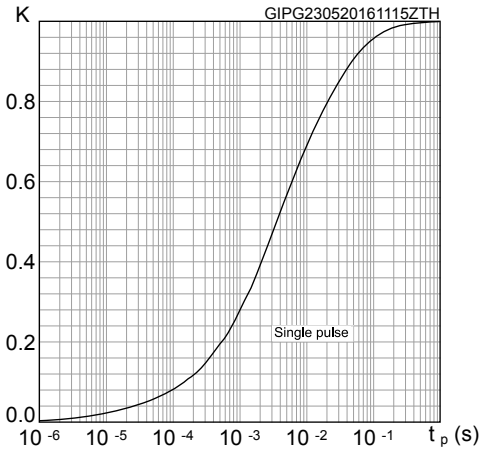


Figure 2. Output characteristics (T_J= 25 °C)

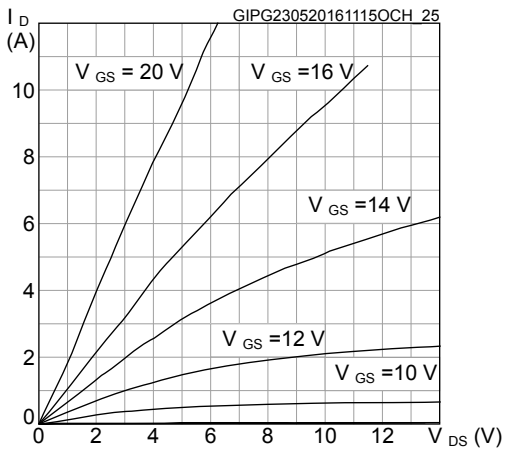


Figure 3. Output characteristics (T_J= 150 °C)

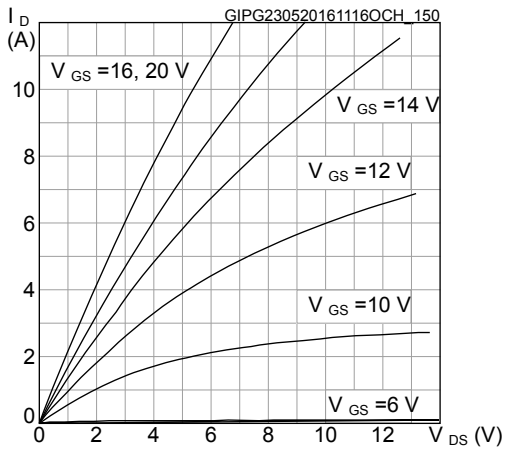


Figure 4. Transfer characteristics

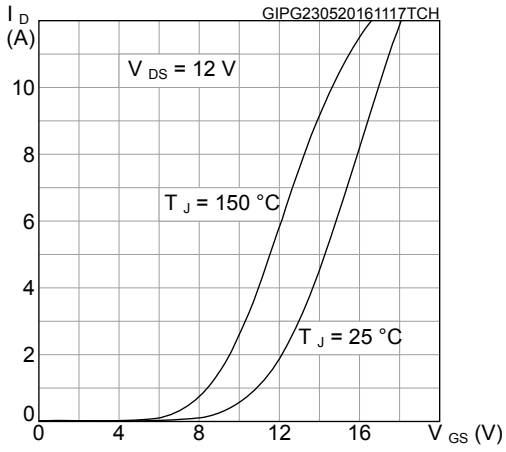


Figure 5. Total power dissipation

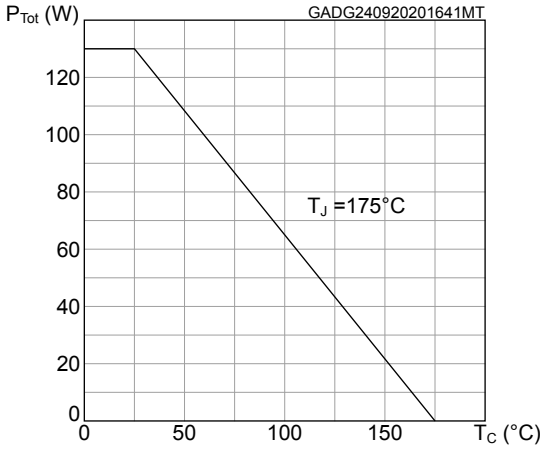


Figure 6. Gate charge vs gate-source voltage

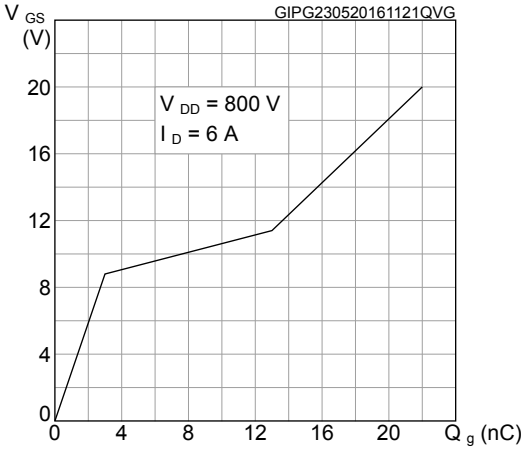


Figure 7. Capacitance variations

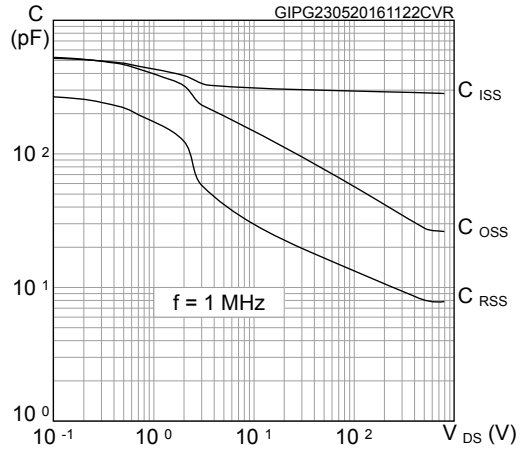


Figure 8. Switching energy vs. drain current

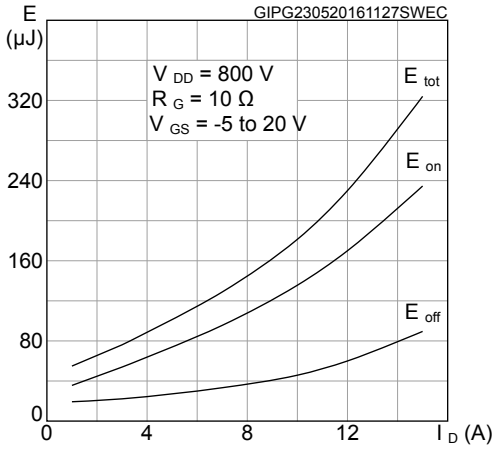


Figure 9. Switching energy vs. junction temperature

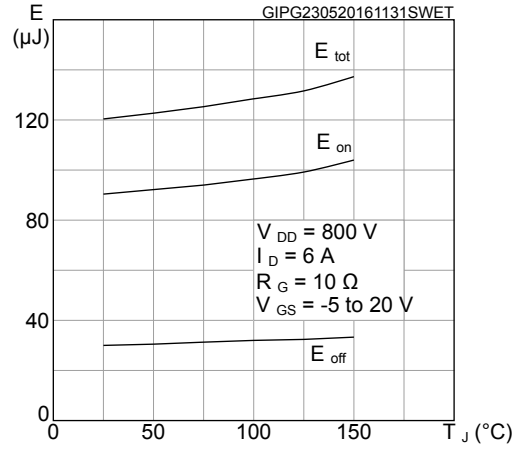


Figure 10. Normalized $V_{(BR)DSS}$ vs. temperature

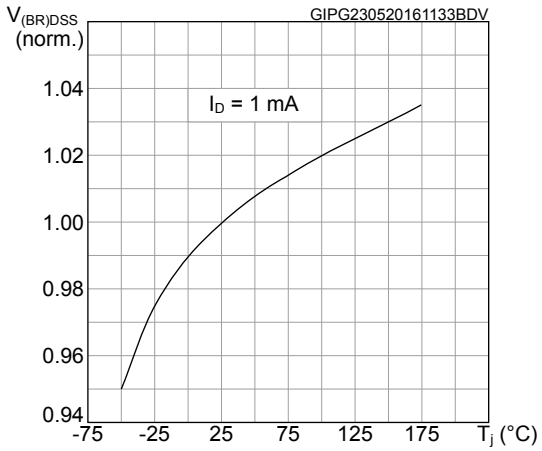


Figure 11. Normalized gate threshold voltage vs. temperature

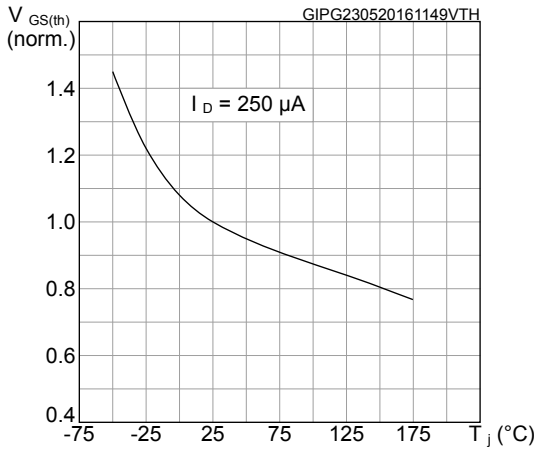


Figure 12. Normalized on-resistance vs. temperature

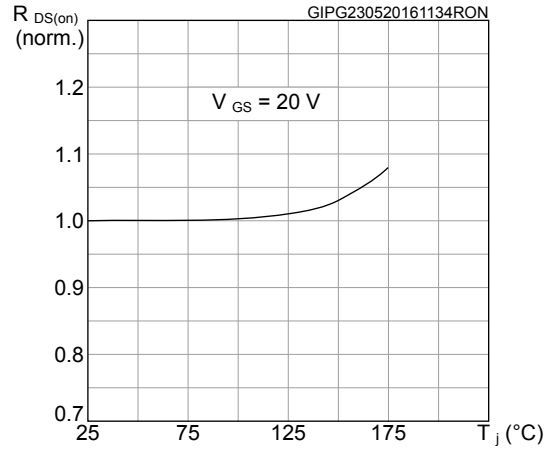


Figure 13. Body diode characteristics (T_J= -50 °C)

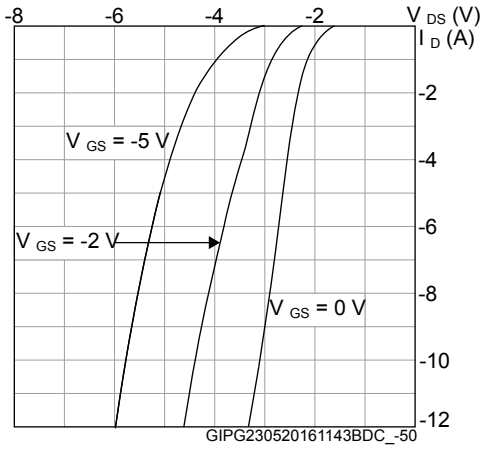


Figure 14. Body diode characteristics (T_J= 25 °C)

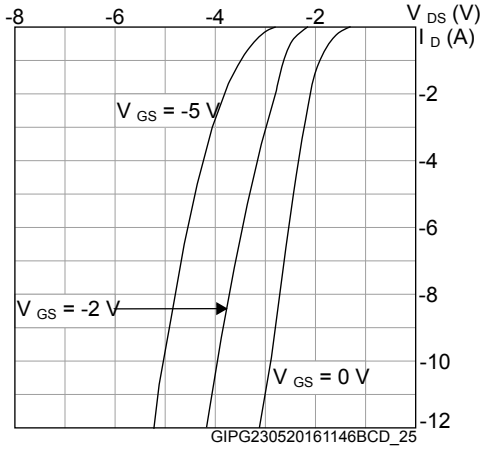


Figure 15. Body diode characteristics (T_J= 150 °C)

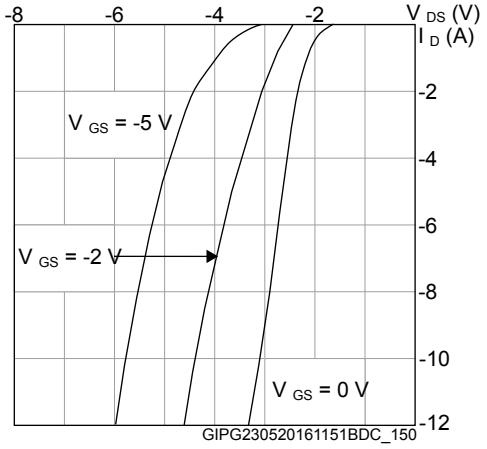


Figure 16. 3rd quadrant characteristics (T_J= -50 °C)

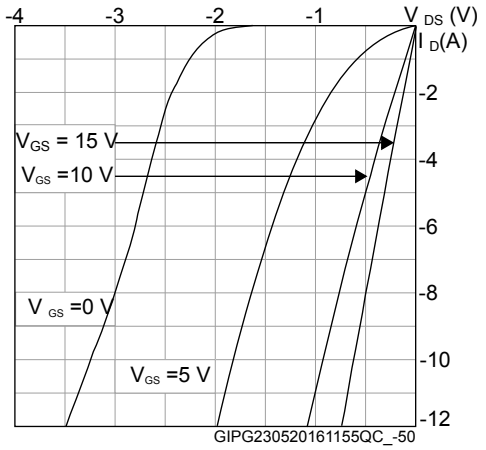


Figure 17. 3rd quadrant characteristics (T_J= 25 °C)

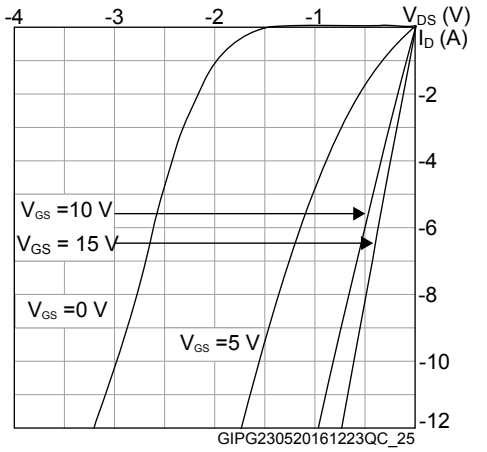
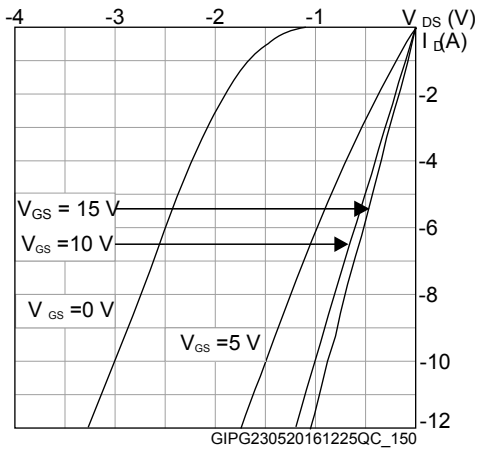
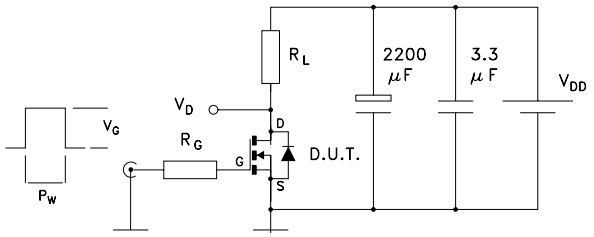


Figure 18. 3rd quadrant characteristics (T_J= 150 °C)



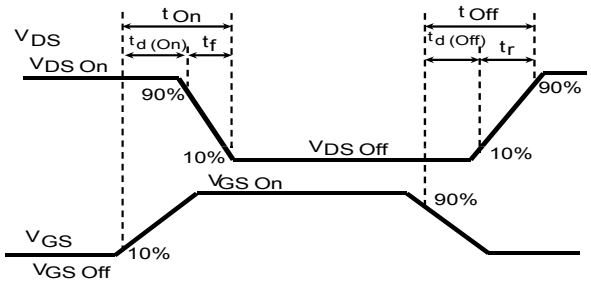
3 Test circuits

Figure 19. Switching test waveforms for transition times



GIPD101020141511FSR

Figure 20. Clamped inductive switching waveform



GIPD101020141502FSR

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 H²PAK-2 package information

Figure 21. H²PAK-2 package outline

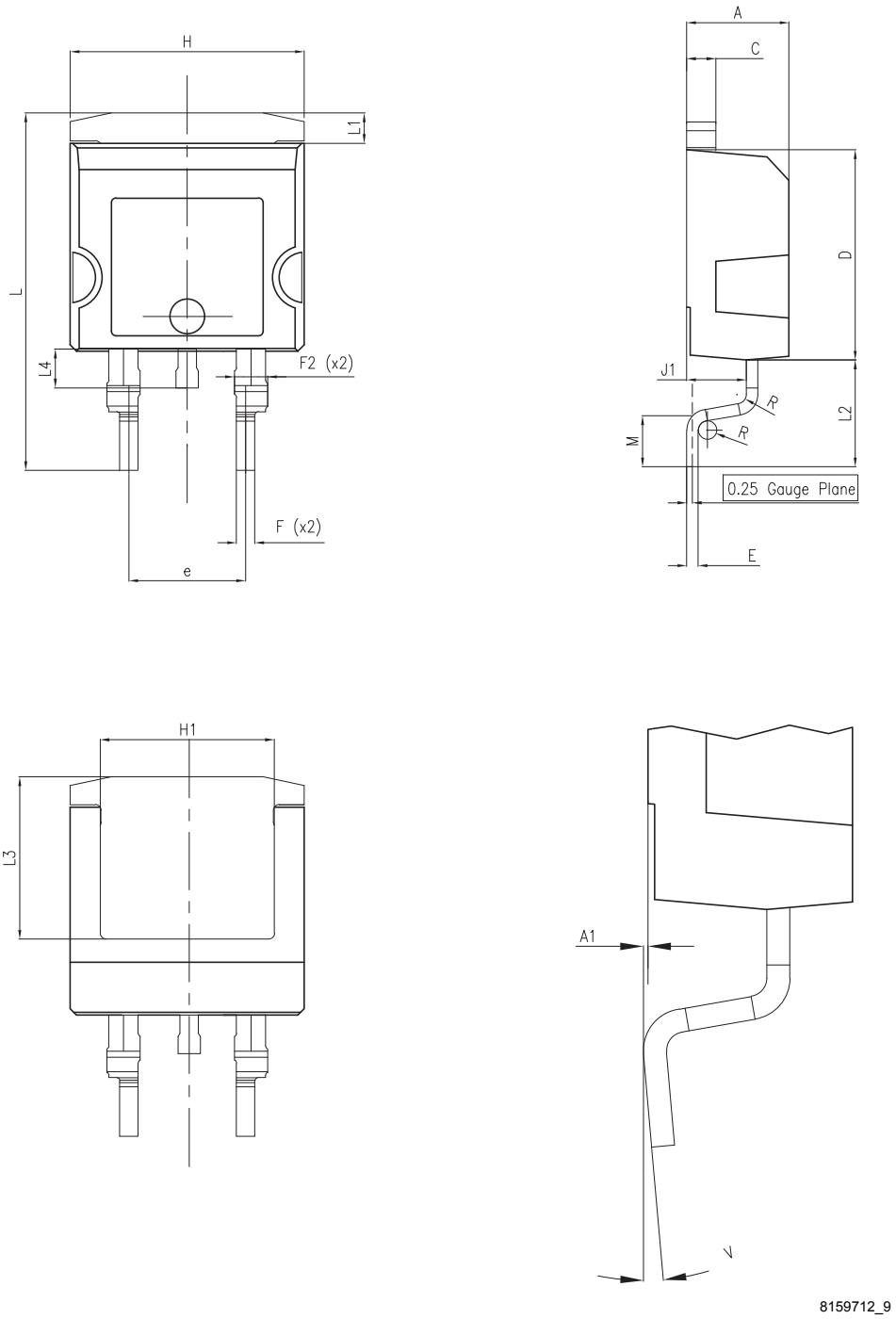
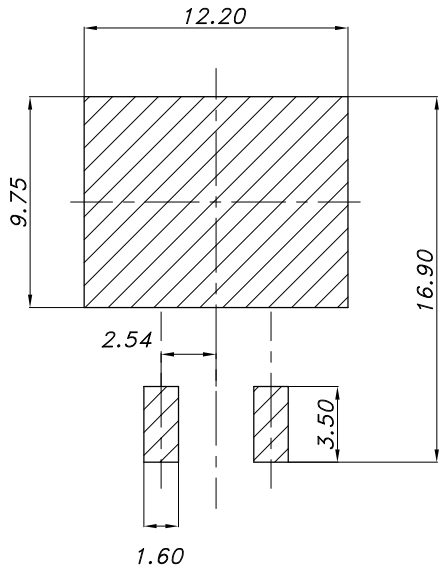


Table 8. H²PAK-2 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
D	8.95		9.35
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
F2	1.14		1.70
H	10.00		10.40
H1	7.40	-	7.80
J1	2.49		2.69
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.50		1.70
M	2.60		2.90
R	0.20		0.60
V	0°		8°

Figure 22. H²PAK-2 recommended footprint



8159712_9

Note: Dimensions are in mm.

4.2 Packing information

Figure 23. **Tape outline**

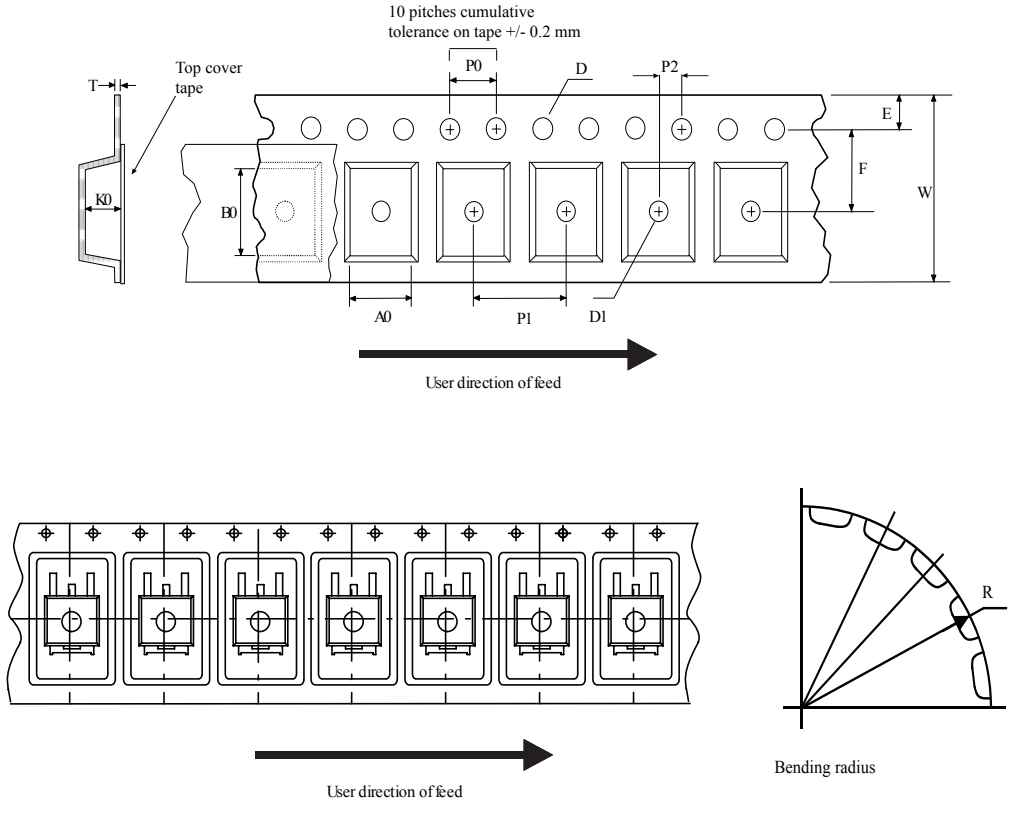


Figure 24. **Reel outline**

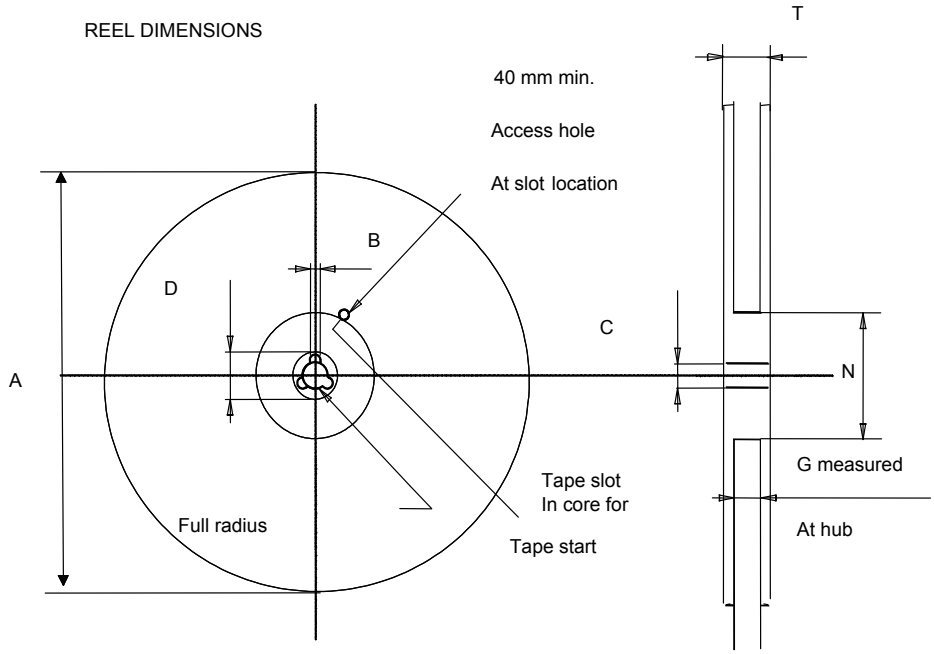


Table 9. **Tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Revision history

Table 10. **Document revision history**

Date	Revision	Changes
05-Oct-2020	1	First release

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